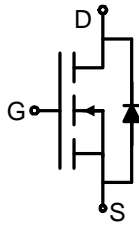



<p>Description The XM2N200. uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● <table border="1" style="display: inline-table; border-collapse: collapse; text-align: center;"> <tr> <td style="padding: 2px 5px;">V_{DSS}</td> <td style="padding: 2px 5px;">$R_{DS(ON)}$ @ 10V (typ)</td> <td style="padding: 2px 5px;">I_D</td> </tr> <tr> <td style="padding: 2px 5px;">190V</td> <td style="padding: 2px 5px;">356.6 mΩ</td> <td style="padding: 2px 5px;">2A</td> </tr> </table> ● High density cell design for ultra low R_{dson} ● Fully characterized avalanche voltage and current ● Excellent package for good heat dissipation ● RoHS Compliant <p>Application</p> <ul style="list-style-type: none"> ● Power switching application ● Hard switched and high frequency circuits ● Uninterruptible power supply 	V_{DSS}	$R_{DS(ON)}$ @ 10V (typ)	I_D	190V	356.6 mΩ	2A	<div style="text-align: center;">  <p>Schematic diagram</p>  <p>TO-92</p> </div>
V_{DSS}	$R_{DS(ON)}$ @ 10V (typ)	I_D					
190V	356.6 mΩ	2A					

Ordering Information

Part Number	Marking	Case	Packaging
XM2N200.	XM2N200.	TO-92	1000pcs/Carton

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	190	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	2	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	8	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.7	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	190	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=190V, V_{GS}=0V$	-	-	1	μA

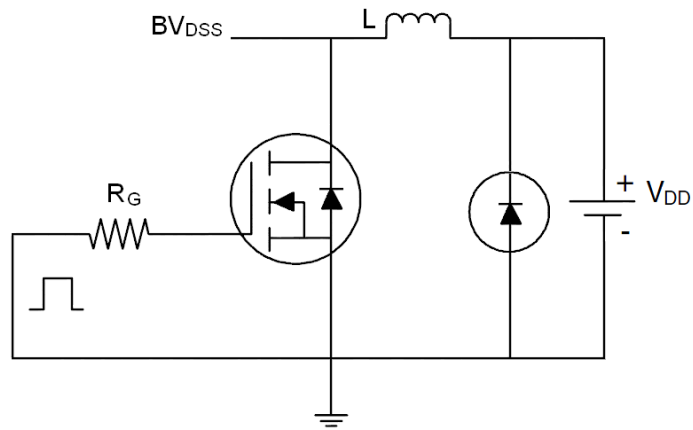
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	2	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	-	356.6	540	m Ω
		$V_{GS}=4.5V, I_D=1A$	-	362.3	560	
Forward Transconductance	g_{FS}	$V_{DS}=15V, I_D=2A$	-	8	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	1325	-	PF
Output Capacitance	C_{OSS}		-	90	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	3	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=100V, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	12	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	t_f		-	15	-	nS
Total Gate Charge	Q_g	$V_{DS}=100V, I_D=2A,$ $V_{GS}=10V$	-	12	-	nC
Gate-Source Charge	Q_{gs}		-	2.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	12	V
Diode Forward Current ^(Note 2)	I_S		-	-	2	A

Notes:

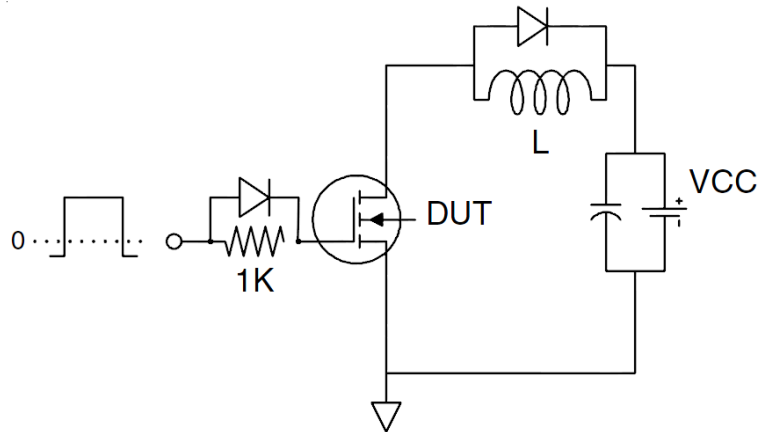
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

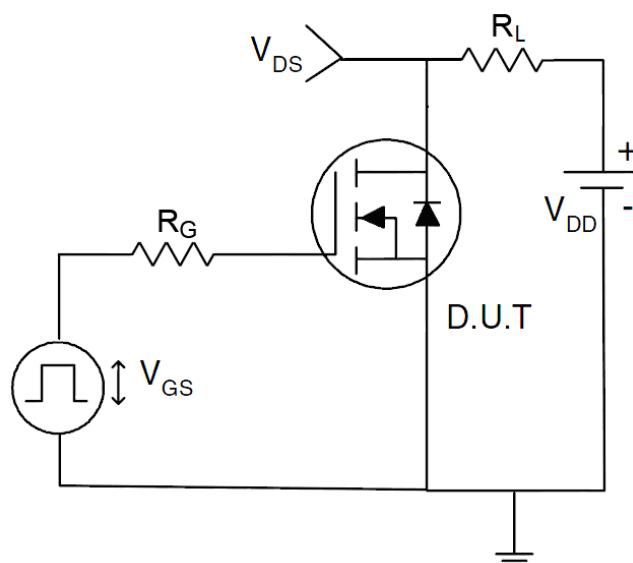
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

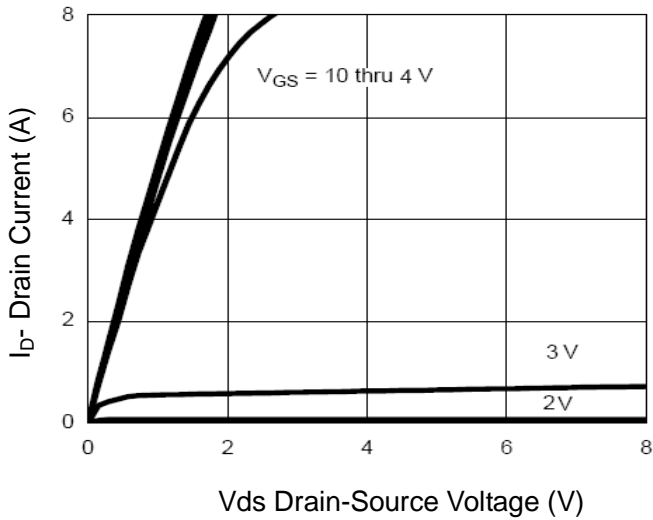


Figure 1 Output Characteristics

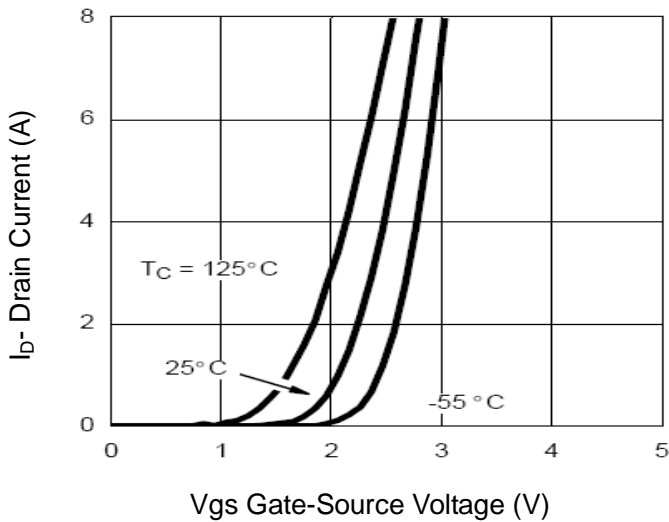


Figure 2 Transfer Characteristics

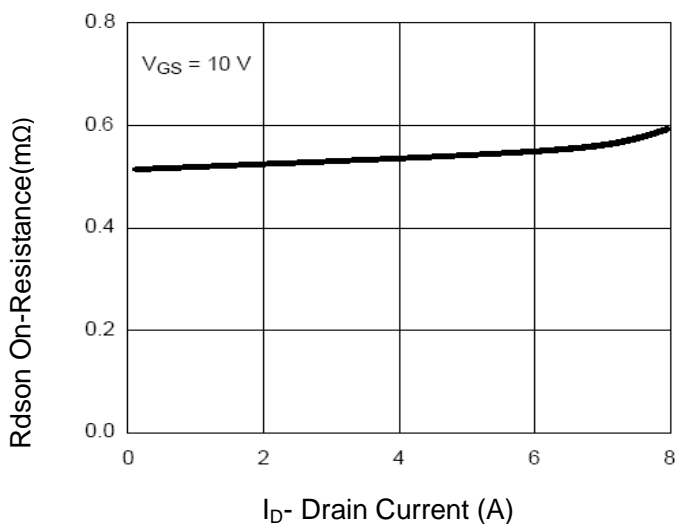


Figure 3 $R_{DS(on)}$ - Drain Current

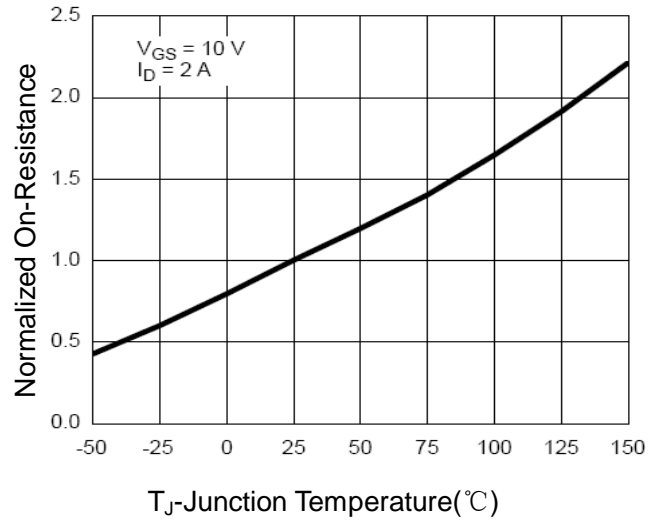


Figure 4 $R_{DS(on)}$ -Junction Temperature

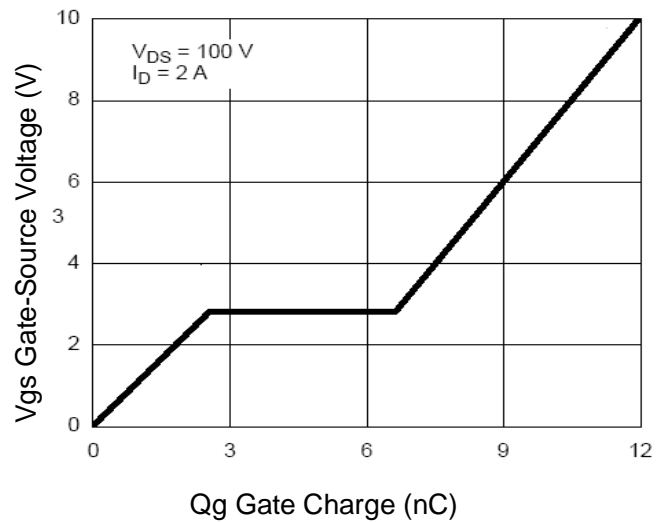


Figure 5 Gate Charge

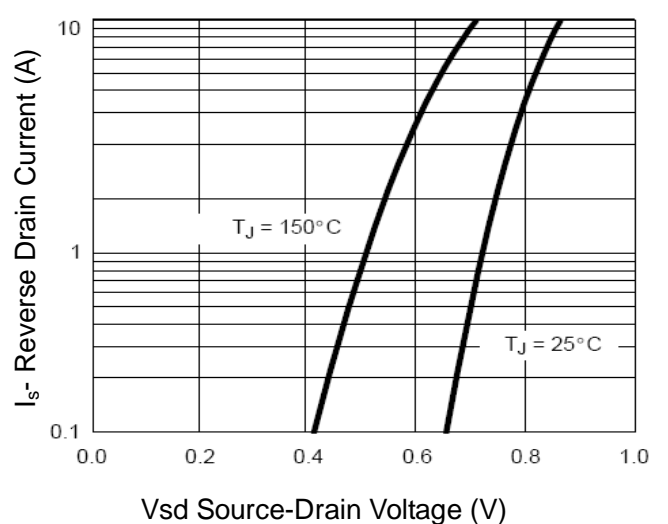


Figure 6 Source- Drain Diode Forward

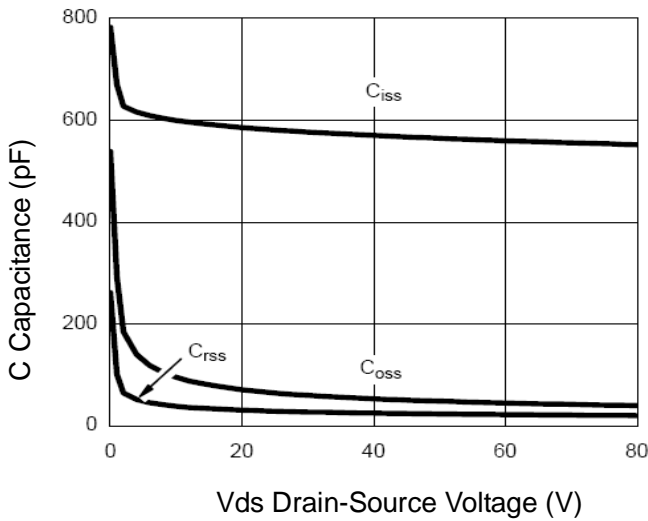


Figure 7 Capacitance vs Vds

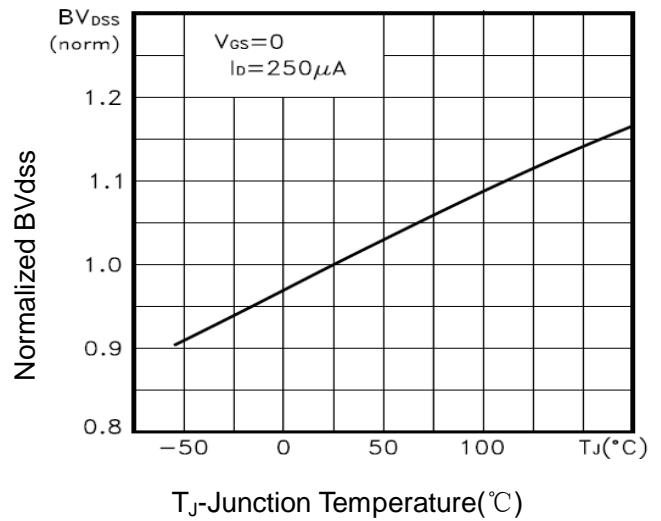


Figure 9 BV_{DSS} vs Junction Temperature

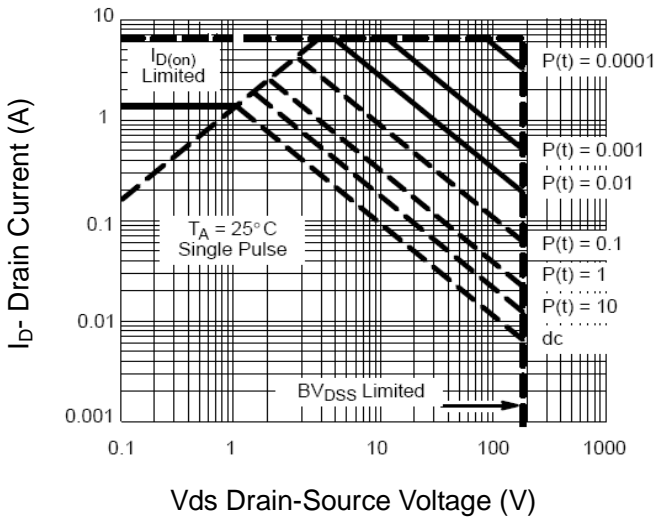


Figure 8 Safe Operation Area

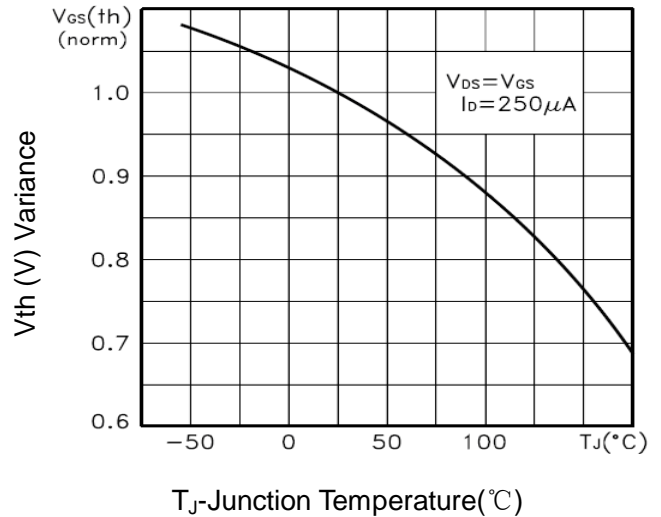


Figure 10 $V_{GS(th)}$ vs Junction Temperature

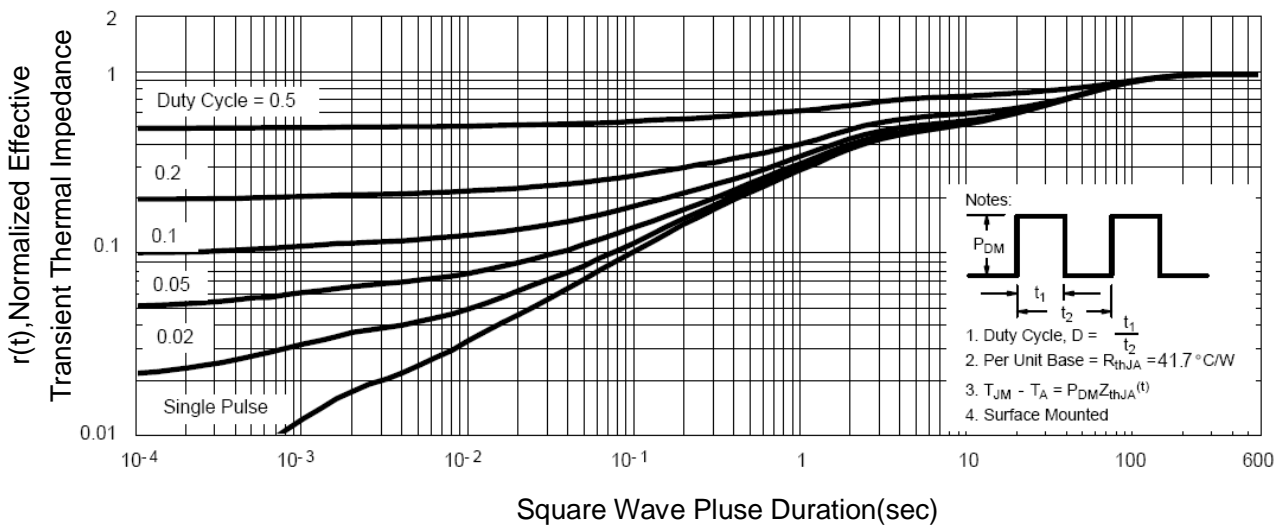
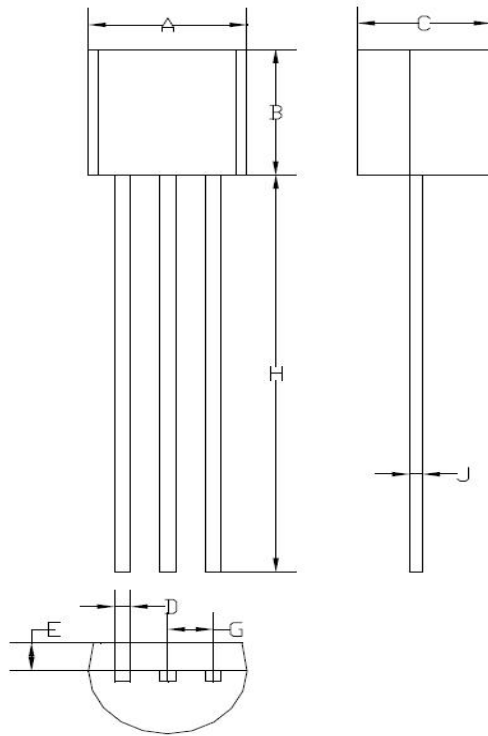


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-92 package information



TO-92			
Dim	MIN	NOM	MAX
A	4.59	4.60	-
B	4.58	4.60	4.62
C	3.50	3.55	3.60
D	2.50	2.55	2.60
E	-	1.25	1.30
G	1.24	1.27	1.30
H	14.28	14.30	14.32
J	0.38		
All Dimensions in mm			